

Product Overview

NGTG40N120FL2: IGBT, 1200V 40A SOLAR/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Optimized for High Speed Switching
- 10 s Short Circuit Capability
- These are Pb-Free Devices

Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Welding

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)/C}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Pack age Type
NGTG40N120FL2WG	Pb-free Halide free	Active	1200	40	2	-	1.1	3.4	-	-	313	10	-	535	No	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

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